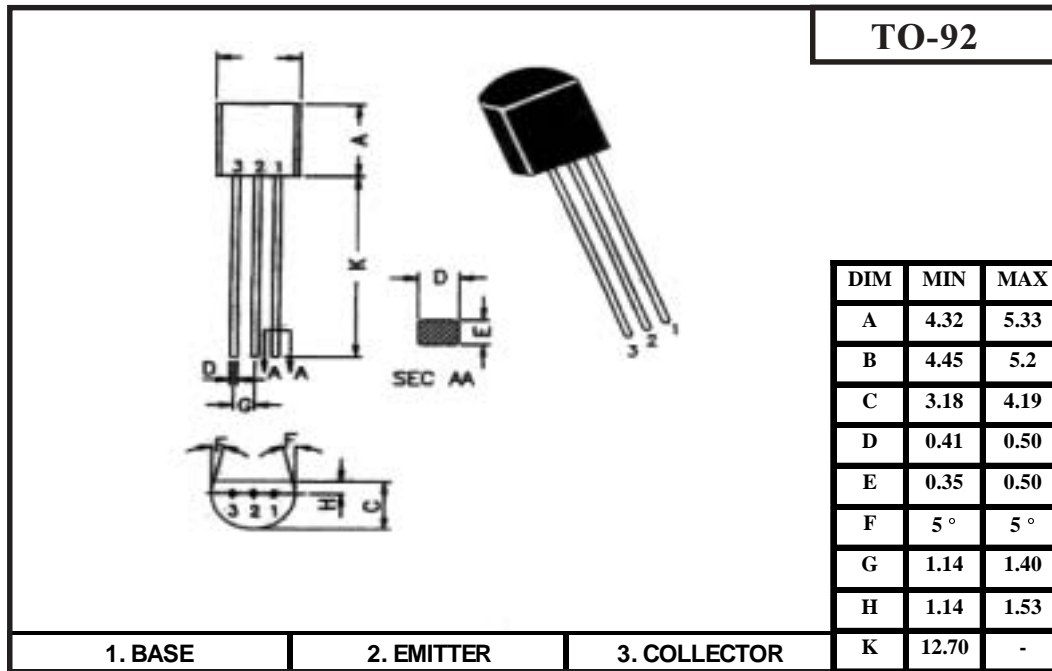


PNP Planar Epitaxial Transistor



Absolute Maximun Ratings (Ta=25°C)

	Symbol		Ratings	Unit
Collector-Emmitter Voltage	V_{CEO}		30	V
Collector Base Voltage	V_{CBO}		35	V
Emitter Base Voltage	V_{EBO}		5	V
Collector current	I_C		800	mA
Emitter Current	I_{EM}		800	mA
Collector Power Dissipation	P_C		600	mW
Operating and Storage Junction	T_j T_{stg}		-50 to +150	°C
Temperature Range				

Characteristics Ratings

(at $T_a = 25^\circ\text{C}$ unless otherwise specified)

	Symbol	Test Conditions	min.	Typ.	max.	Unit
Collector Emitter Voltage	V_{CEO}	$I_C = 10\text{mA}, I_B = 0$	30			V
Collector Cut off Current	I_{CBO}	$V_C = 35\text{V}, I_E = 0$			0.1	μA
Emitter Cut off Current	I_{EBO}	$V_{EB} = 5\text{V}, I_C = 0$			0.1	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE} = 1\text{V}, I_C = 100\text{mA}$	100		320	
	$h_{FE(2)}$	$V_{CE} = 1\text{V}, I_C = 700\text{mA}$	35			
Collector Emitter Saturation Voltage	$V_{CE(SAT)}^*$	$I_C = 500\text{mA}, I_B = 20\text{mA}$			0.7	V
Base Emitter on Voltage	$V_{BE(on)}$	$V_{CE} = 5\text{V}, I_C = 10\text{mA}$	0.5		0.8	
Transition Frequency	f_T	$I_C = 10\text{mA}, V_{CE} = 5\text{V}$		120		MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$		19		pF

* Pulse Condition: Width $\leq 300\text{ms}$, Duty Cycle $\leq 2\%$